

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	2.8	A
		T _A = +70°C		2.2	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.1	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	12	A

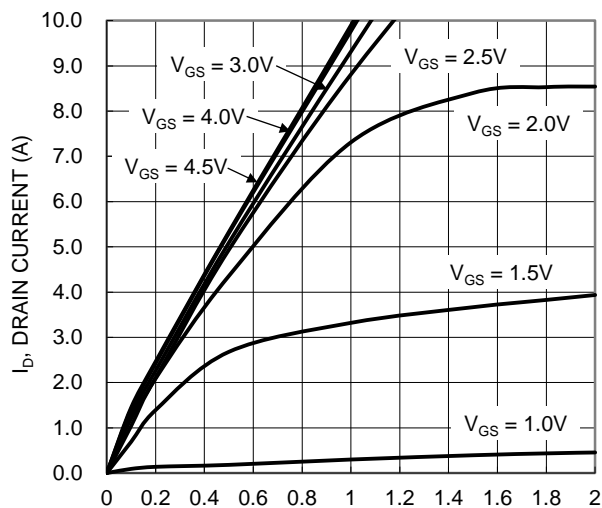
Thermal Characteristics

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P _D	0.66	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	192	°C/W
Total Power Dissipation (Note 6)			P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	115	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

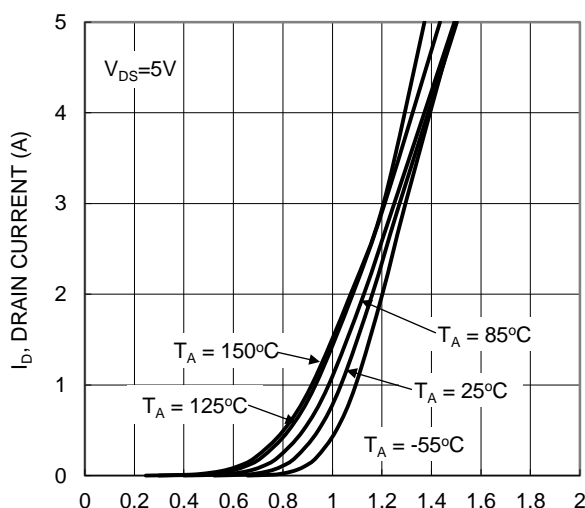
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	10	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	0.6	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	61	90	mΩ	V _{GS} = 4.5V, I _D = 3.6A
			80	120		V _{GS} = 2.5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	130	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	26	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	18	—	pF	
Gate Resistance	R _G	—	2.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	1.4	—	nC	V _{DS} = 10V, I _D = 3.6A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	2.8	—	nC	
Gate-Source Charge	Q _{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q _{GD}	—	0.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	0.6	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _G = 1Ω, R _L = 2.78Ω
Turn-On Rise Time	t _R	—	2.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	4.2	—	ns	
Turn-Off Fall Time	t _F	—	1.7	—	ns	
Reverse Recovery Time	t _{RR}	—	5.3	—	ns	I _F = 3.6A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	0.5	—	nC	I _F = 3.6A, di/dt = 100A/μs

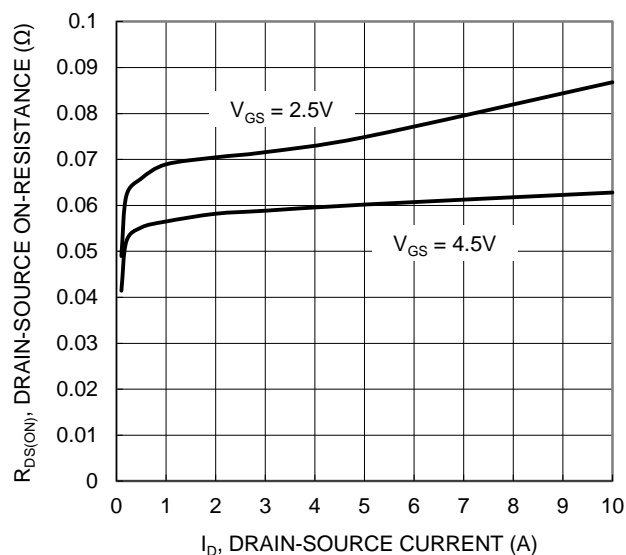
- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.



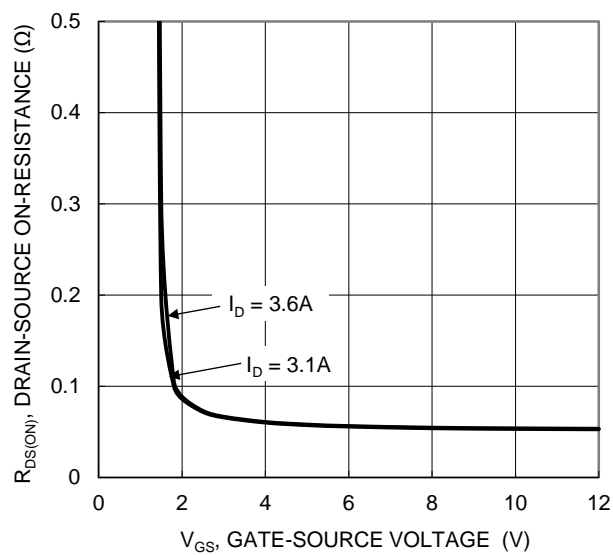
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 1. Typical Output Characteristic



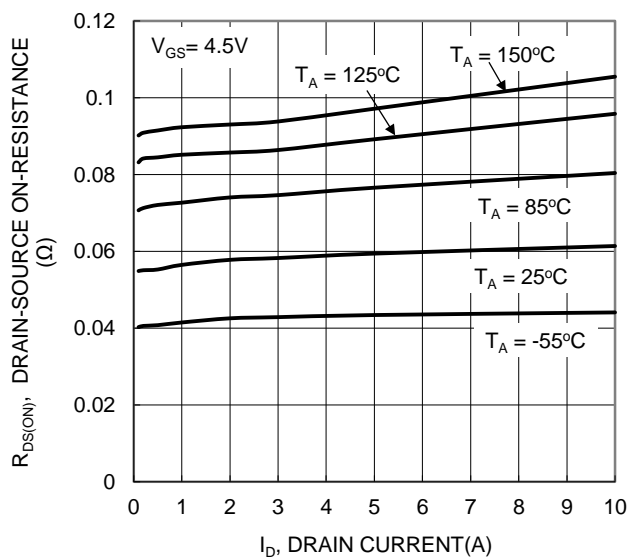
V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 2. Typical Transfer Characteristic



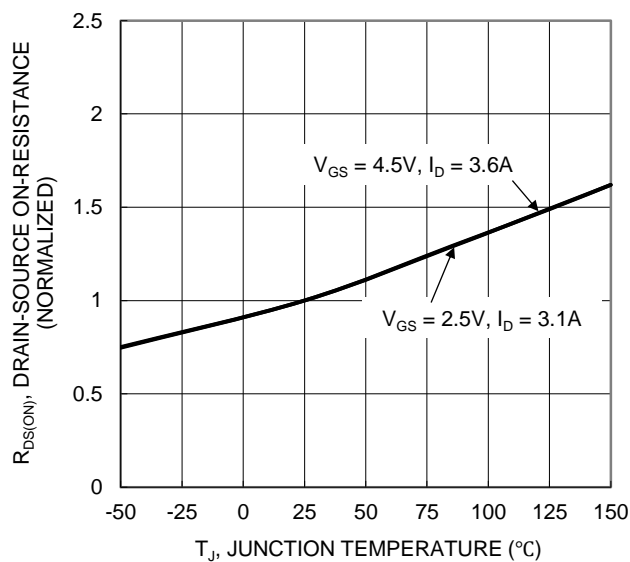
I_D , DRAIN-SOURCE CURRENT (A)
Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage



V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 4. Typical Transfer Characteristic



I_D , DRAIN CURRENT(A)
Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature



T_J , JUNCTION TEMPERATURE (°C)
Figure 6. On-Resistance Variation with Junction Temperature

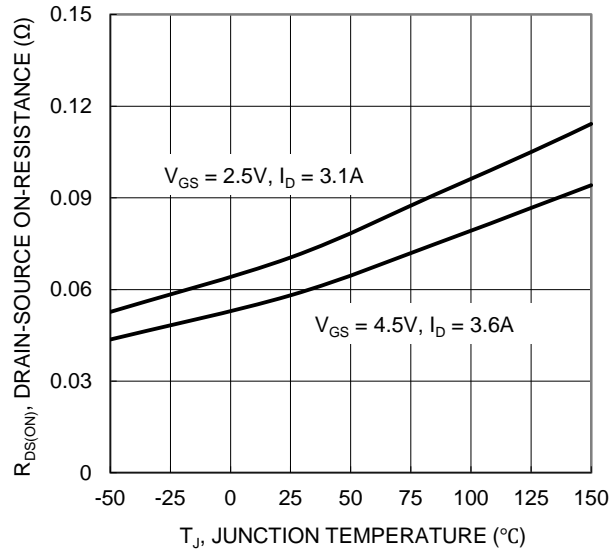


Figure 7. On-Resistance Variation with Junction Temperature

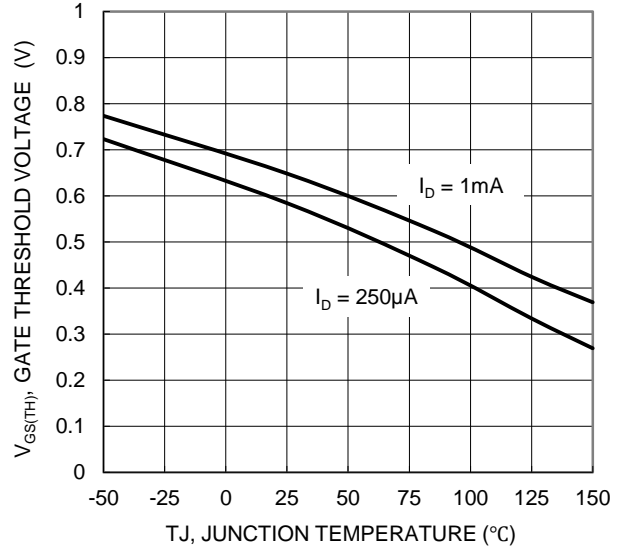


Figure 8. Gate Threshold Variation vs Junction Temperature

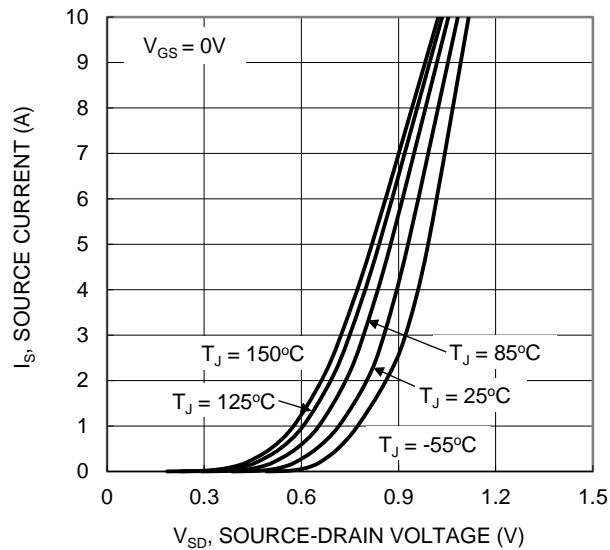


Figure 9. Diode Forward Voltage vs. Current

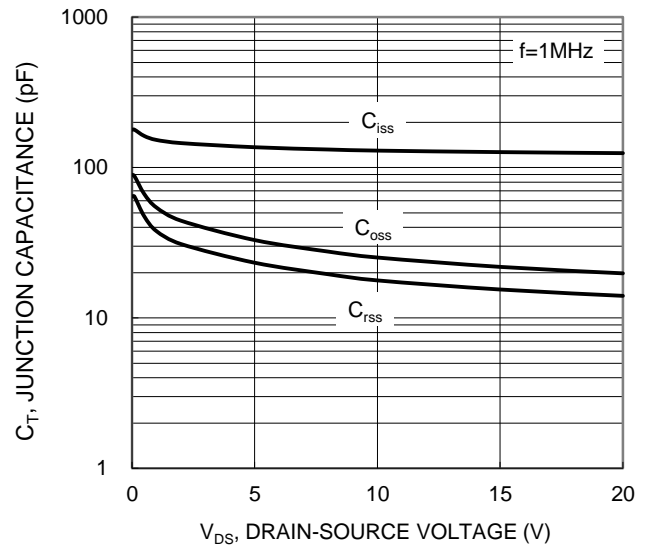


Figure 10. Typical Junction Capacitance

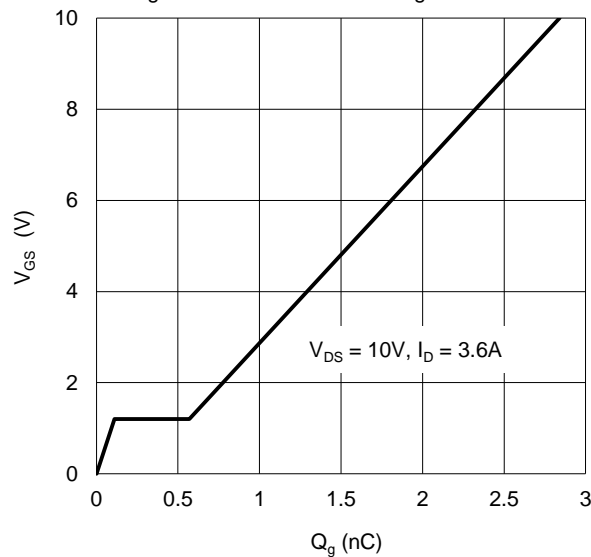


Figure 11. Gate Charge

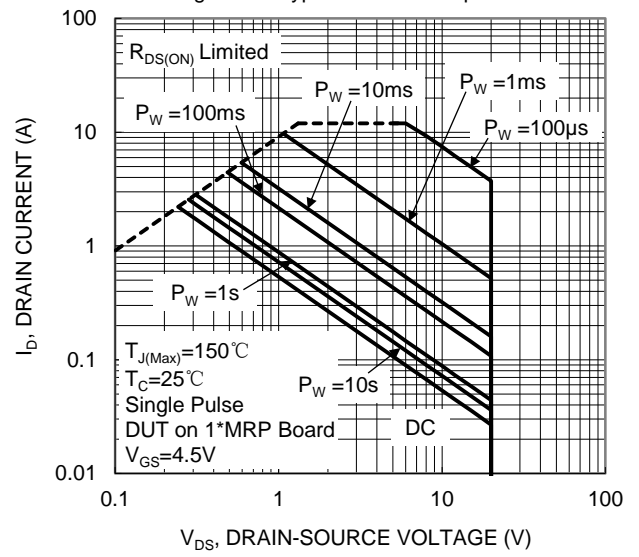


Figure 12. SOA, Safe Operation Area

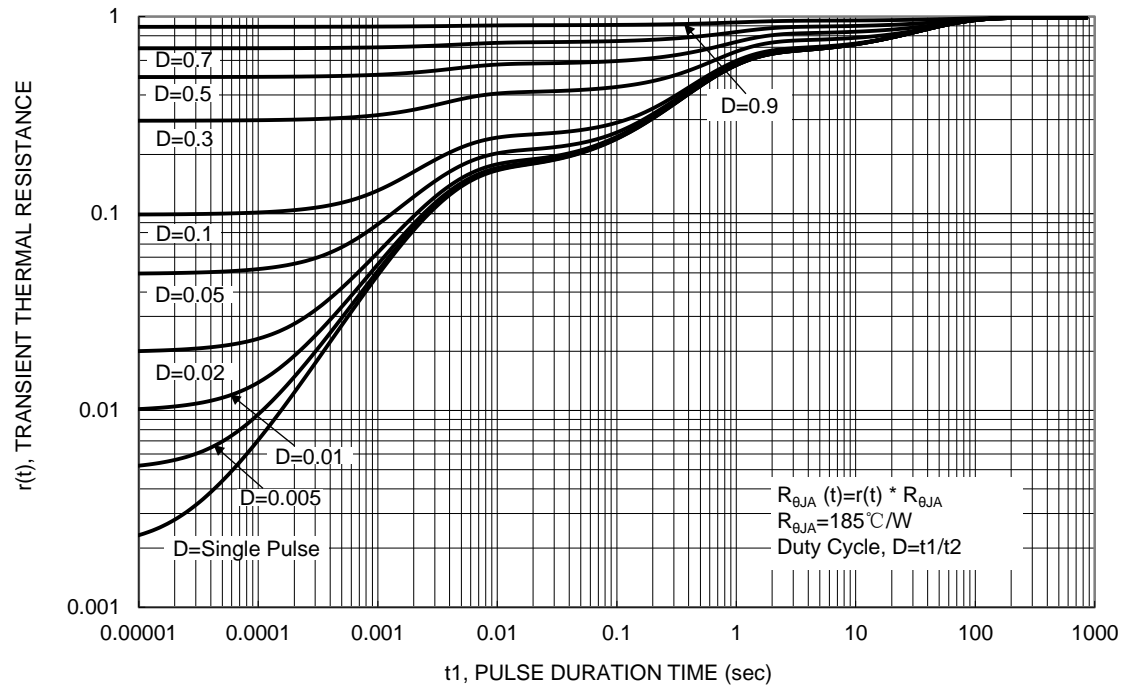
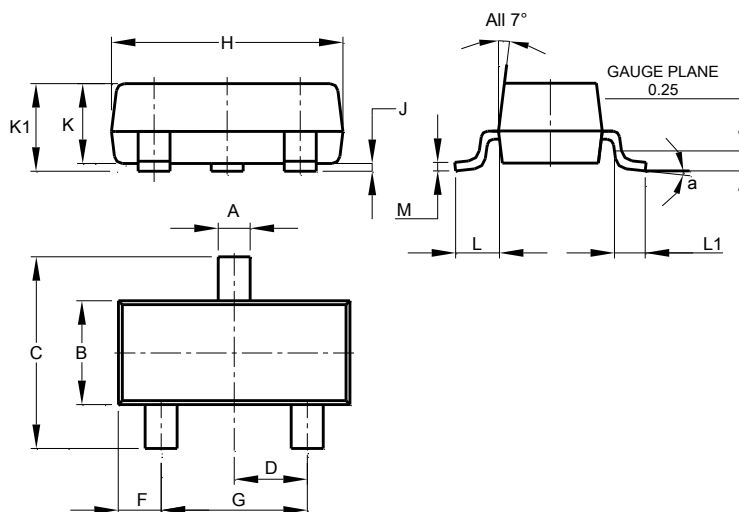


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23

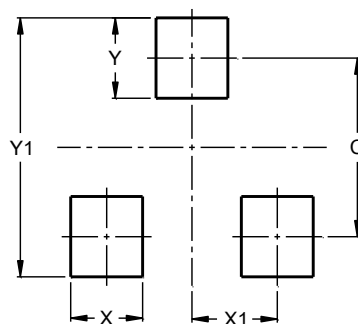


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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